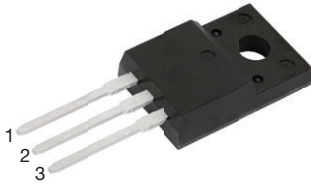
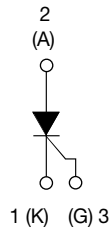


Thyristor High Voltage, Phase Control SCR, 25 A



3L TO-220 FullPAK



FEATURES

- Designed and qualified for industrial level
- Fully isolated package ($V_{INS} = 2500 V_{RMS}$)
- UL pending
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see EKOWEISS Semiconductors



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

DESCRIPTION

The EKS-25TTS...FP... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

PRIMARY CHARACTERISTICS

$I_{T(AV)}$	16 A
V_{DRM}/V_{RRM}	800 V, 1200 V
V_{TM}	1.25 V
I_{GT}	45 mA
T_J	-40 °C to 125 °C
Package	3L TO-220 FullPAK
Circuit configuration	Single SCR

OUTPUT CURRENT IN TYPICAL APPLICATIONS

APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W	18	22	A

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	16	A
I_{RMS}		25	
V_{RRM}/V_{DRM}		800, 1200	V
I_{TSM}		350	A
V_T	16 A, $T_J = 25$ °C	1.25	V
dV/dt		500	V/μs
dI/dt		150	A/μs
T_J		-40 to +125	°C

VOLTAGE RATINGS

PART NUMBER	V_{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V_{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I_{RRM}/I_{DRM} AT 125 °C mA
EKS-25TTS08FP-M3	800	800	10
EKS-25TTS12FP-M3	1200	1200	

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS	
			TYP.	MAX.		
Maximum average on-state current	$I_{T(AV)}$	$T_C = 51\text{ }^\circ\text{C}$, 180° conduction half sine wave	16		A	
Maximum RMS on-state current	I_{RMS}		25			
Maximum peak, one-cycle, non-repetitive surge current	I_{TSM}	10 ms sine pulse, rated V_{RRM} applied	300			
		10 ms sine pulse, no voltage reapplied	350			
Maximum I^2t for fusing	I^2t	10 ms sine pulse, rated V_{RRM} applied	450		A^2s	
		10 ms sine pulse, no voltage reapplied	630			
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1\text{ms}$ to 10 ms, no voltage reapplied	6300		$A^2\sqrt{s}$	
Maximum on-state voltage drop	V_{TM}	16 A, $T_J = 25\text{ }^\circ\text{C}$	1.25		V	
On-state slope resistance	r_t	$T_J = 125\text{ }^\circ\text{C}$	12.0		$m\Omega$	
Threshold voltage	$V_{T(TO)}$		1.0		V	
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	$V_R = \text{Rated } V_{RRM}/V_{DRM}$	$T_J = 25\text{ }^\circ\text{C}$	0.5		mA
			$T_J = 125\text{ }^\circ\text{C}$	10		
Holding current	I_H	Anode supply = 6 V, resistive load, initial $I_T = 1\text{ A}$, $T_J = 25\text{ }^\circ\text{C}$	-	150	mA	
Maximum latching current	I_L	Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	200			
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_{J\text{ max.}}$, linear to 80 %, $V_{DRM} = R_g - k = \text{Open}$	500		$V/\mu s$	
Maximum rate of rise of turned-on current	dI/dt		150		$A/\mu s$	

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P_{GM}		8.0	W	
Maximum average gate power	$P_{G(AV)}$		2.0		
Maximum peak positive gate current	$+I_{GM}$		1.5	A	
Maximum peak negative gate voltage	$-V_{GM}$		10	V	
Maximum required DC gate current to trigger	I_{GT}	Anode supply = 6 V, resistive load, $T_J = -10\text{ }^\circ\text{C}$	60		mA
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	45		
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$	20		
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, $T_J = -10\text{ }^\circ\text{C}$	2.5		V
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	2.0		
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$	1.0		
Maximum DC gate voltage not to trigger	V_{GD}	$T_J = 125\text{ }^\circ\text{C}$, $V_{DRM} = \text{Rated value}$	0.25		mA
Maximum DC gate current not to trigger	I_{GD}		2.0		

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t_{gt}	$T_J = 25\text{ }^\circ\text{C}$	0.9	μs
Typical reverse recovery time	t_{rr}	$T_J = 125\text{ }^\circ\text{C}$	4	
Typical turn-off time	t_q		110	

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T_J, T_{Stg}		-40 to 125	°C
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	2.5	°C/W
Maximum thermal resistance, junction to ambient	R_{thJA}		62	
Typical thermal resistance, case to heatsink	R_{thCS}	Mounting surface, smooth, and greased	0.5	
Approximate weight			2	g
			0.07	oz.
Mounting torque	minimum		6 (5)	kgf · cm (lbf · in)
	maximum		12 (10)	
Marking device		Case style 3L TO-220 FullPAK	25TTS08FP	
			25TTS12FP	

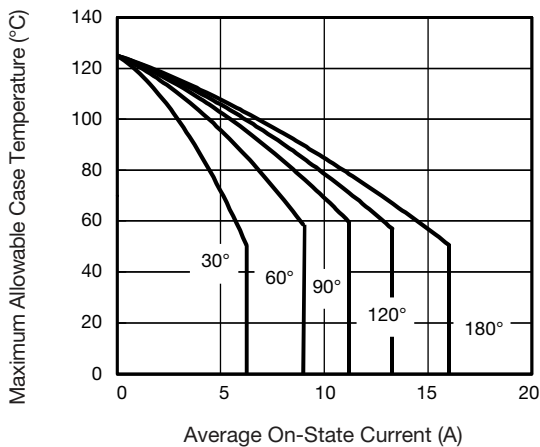


Fig. 1 - Current Rating Characteristics

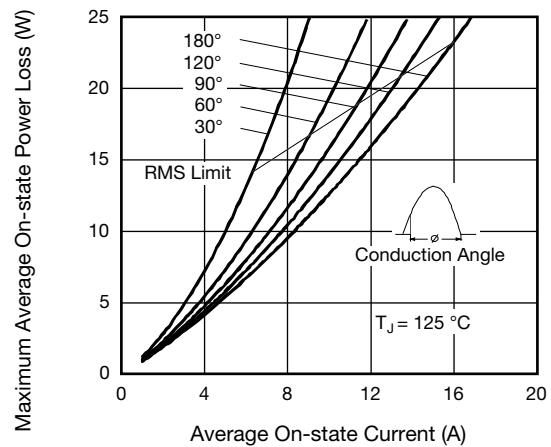


Fig. 3 - On-State Power Loss Characteristics

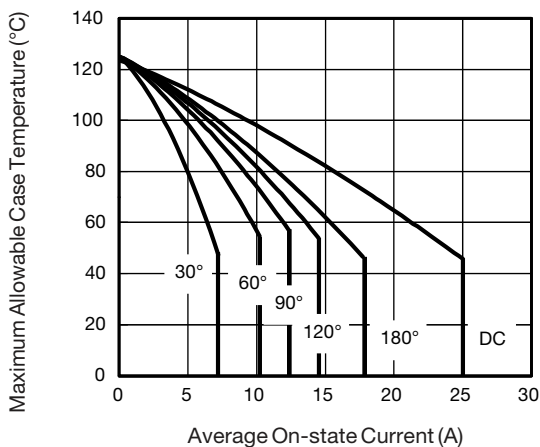


Fig. 2 - Current Rating Characteristics

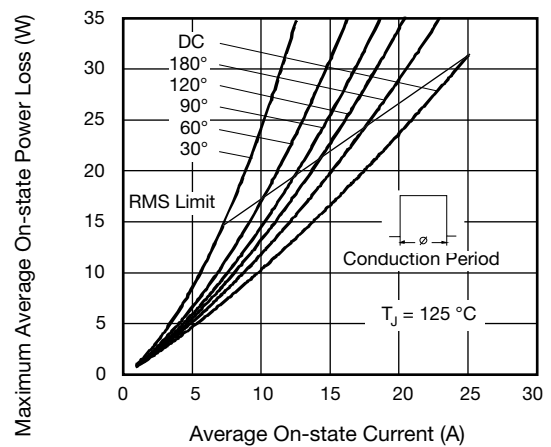


Fig. 4 - On-State Power Loss Characteristics

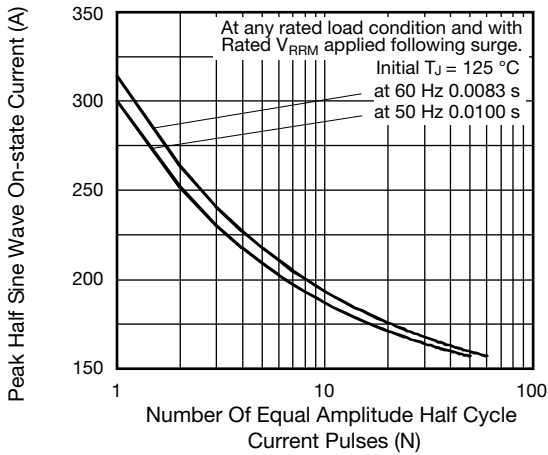


Fig. 5 - Maximum Non-Repetitive Surge Current

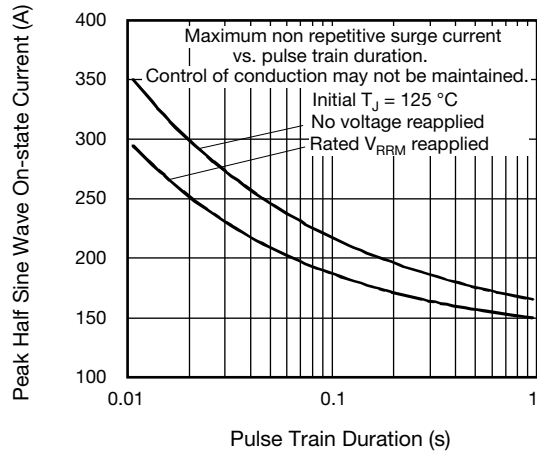


Fig. 6 - Maximum Non-Repetitive Surge Current

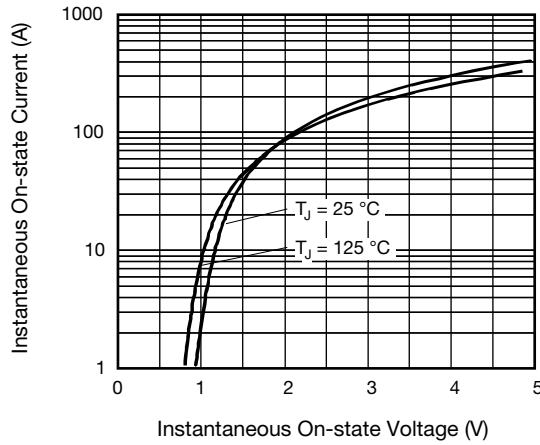


Fig. 7 - On-State Voltage Drop Characteristics

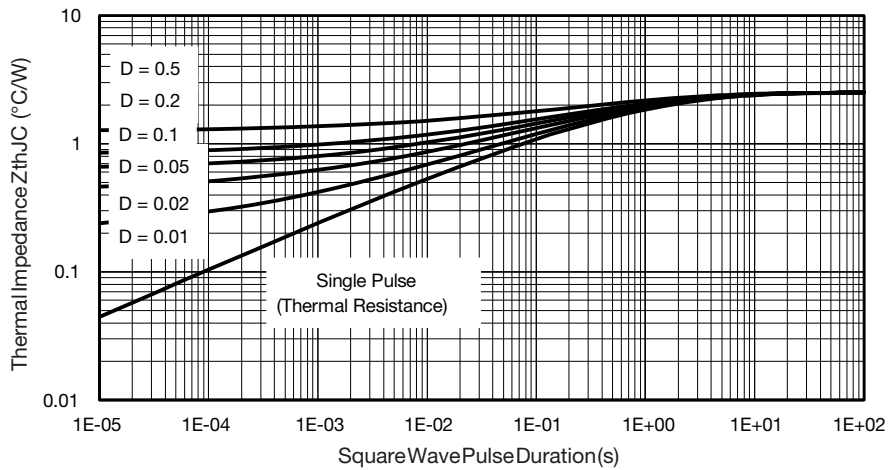


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

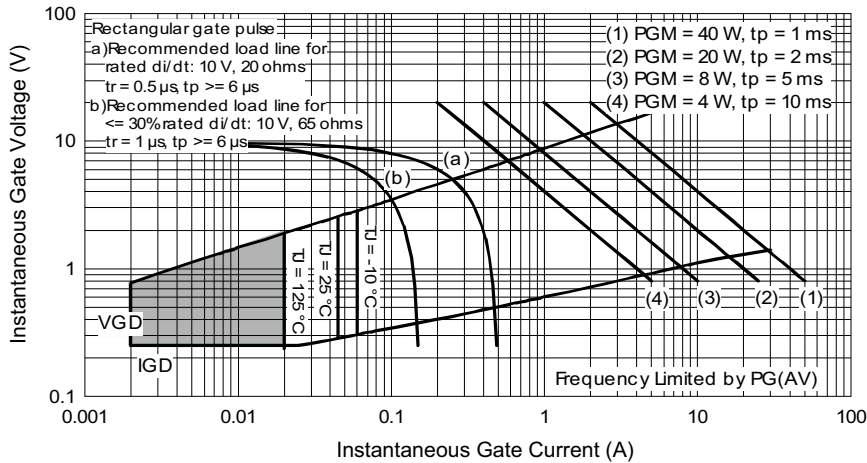


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

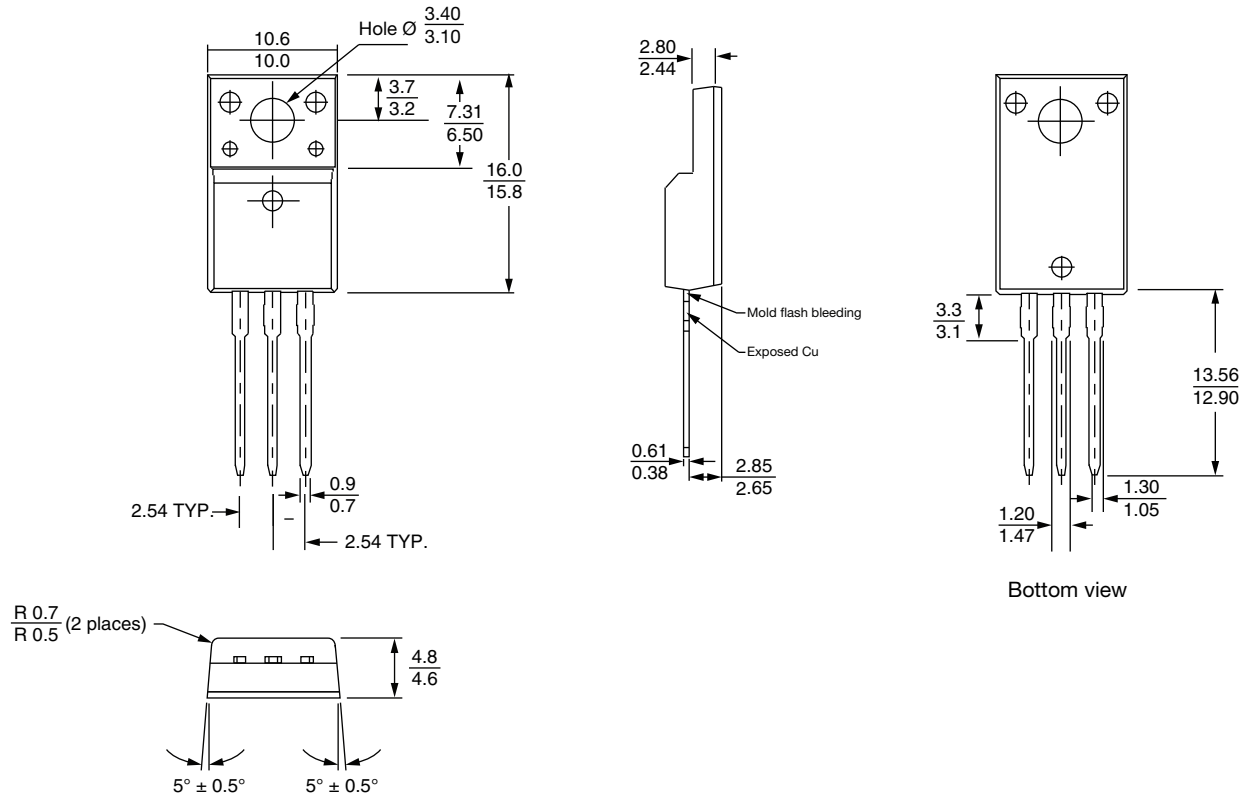
Device code	EKS-	25	T	T	S	12	FP	-M3
	①	②	③	④	⑤	⑥	⑦	⑧
	1	- EKOWEISS Semiconductors product						
	2	- Current rating (25 = 25 A)						
	3	- Circuit configuration: T = single thyristor						
	4	- Package: T = TO-220AB						
	5	- Type of silicon: Standard recovery rectifier						
	6	- Voltage code x 100 = V _{RRM} 08 = 800 V 12 = 1200 V						
	7	- FullPAK						
	8	- Environmental digit: -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free						

ORDERING INFORMATION (Example)			
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
EKS-25TTS08FP-M3	50	1000	Antistatic plastic tubes
EKS-25TTS12FP-M3	50	1000	Antistatic plastic tubes

LINKS TO RELATED DOCUMENTS	
Dimensions	EKOWEISS Semiconductors
Part marking information	EKOWEISS Semiconductors

3L TO-220 FullPAK

DIMENSIONS in millimeters



Notes

- (1) All dimensions are in mm
- (2) Package body size exclude mold flash and burrs. Moldflash should be less than 6 mils

Disclaimer

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